

## Precision CMOS Analog Switches

### Features

- $\pm 15\text{-V}$  Analog Signal Range
- On-Resistance— $r_{DS(on)}$ :  $20\ \Omega$
- Fast Switching Action— $t_{ON}$ :  $100\ \text{ns}$
- Ultra Low Power Requirements— $P_D$ :  $35\ \text{nW}$
- TTL and CMOS Compatible
- MiniDIP and SOIC Packaging
- 44-V Supply Max Rating

### Benefits

- Wide Dynamic Range
- Low Signal Errors and Distortion
- Break-Before-Make Switching Action
- Simple Interfacing
- Reduced Board Space
- Improved Reliability

### Applications

- Precision Test Equipment
- Precision Instrumentation
- Battery Powered Systems
- Sample-and-Hold Circuits
- Military Radios
- Guidance and Control Systems
- Hard Disk Drives

### Description

The DG417/418/419 monolithic CMOS analog switches were designed to provide high performance switching of analog signals. Combining low power, low leakages, high speed, low on-resistance and small physical size, the DG417 series is ideally suited for portable and battery powered industrial and military applications requiring high performance and efficient use of board space.

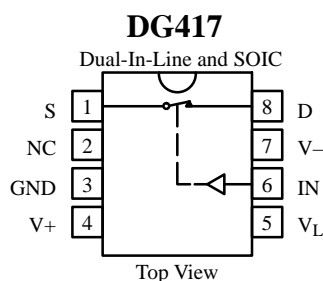
To achieve high-voltage ratings and superior switching performance, the DG417 series is built on Siliconix's high

voltage silicon gate (HVSG) process. Break-before-make is guaranteed for the DG419, which is an SPDT configuration. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

The DG417 and DG418 respond to opposite control logic levels as shown in the Truth Table.

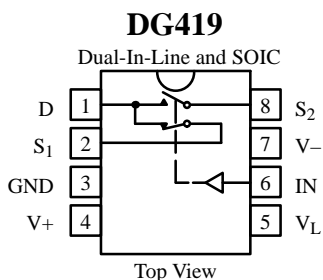
### Functional Block Diagram and Pin Configuration



**Truth Table**

Logic	DG417	DG418
0	ON	OFF
1	OFF	ON

Logic "0" =  $\leq 0.8\ \text{V}$ , Logic "1" =  $\geq 2.4\ \text{V}$



**Truth Table—DG419**

Logic	SW <sub>1</sub>	SW <sub>2</sub>
0	ON	OFF
1	OFF	ON

Logic "0" =  $\leq 0.8\ \text{V}$ , Logic "1" =  $\geq 2.4\ \text{V}$

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70051.

## Ordering Information

Temp Range	Package	Part Number
<b>DG417/418</b>		
-40 to 85°C	8-Pin Plastic MiniDIP	DG417DJ
		DG418DJ
	8-Pin Narrow SOIC	DG417DY
		DG418DY
-55 to 125°C	8-Pin CerDIP	DG417AK, DG417AK/883
		DG418AK, DG418AK/883
<b>DG419</b>		
-40 to 85°C	8-Pin Plastic MiniDIP	DG419DJ
	8-Pin Narrow SOIC	DG419DY
-55 to 125°C	8-Pin CerDIP	DG419AK, DG419AK/883

## Absolute Maximum Ratings

Voltages Referenced to V-

V+	44 V
GND	25 V
V <sub>L</sub>	(GND - 0.3 V) to (V+) + 0.3 V
Digital Inputs <sup>a</sup> V <sub>S</sub> , V <sub>D</sub>	(V-) - 2 V to (V+) + 2 V or 30 mA, whichever occurs first
Current, (Any Terminal) Continuous	30 mA
Current (S or D) Pulsed 1 ms, 10% duty cycle	100 mA
Storage Temperature (AK Suffix)	-65 to 150°C
(DJ, DY Suffix)	-65 to 125°C

Power Dissipation (Package)<sup>b</sup>

8-Pin Plastic MiniDIP <sup>c</sup>	400 mW
8-Pin Narrow SOIC <sup>d</sup>	400 mW
8-Pin CerDIP <sup>e</sup>	600 mW

Notes:

- Signals on S<sub>X</sub>, D<sub>X</sub>, or IN<sub>X</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- All leads welded or soldered to PC Board.
- Derate 6 mW/°C above 75°C
- Derate 6.5 mW/°C above 25°C
- Derate 12 mW/°C above 75°C

## Schematic Diagram (Typical Channel)

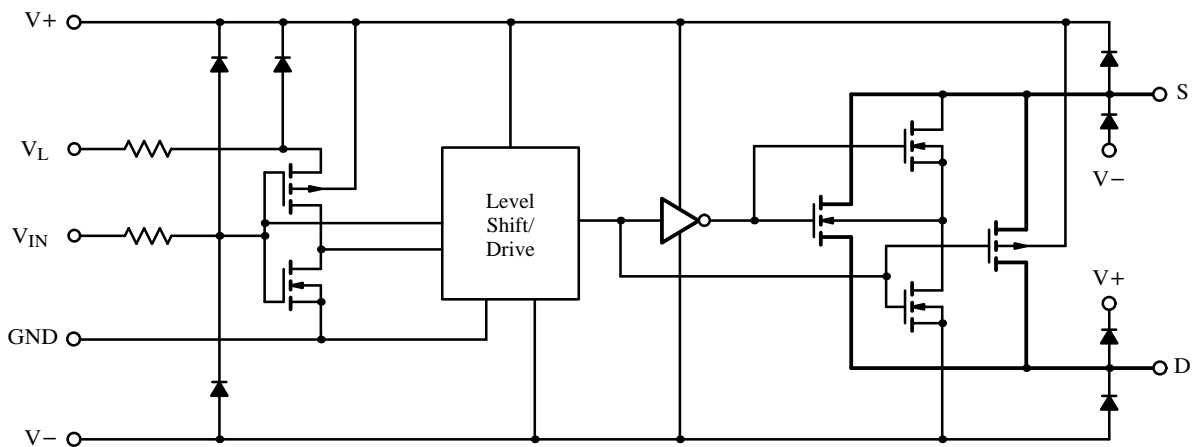


Figure 1.

## Specifications<sup>a</sup>

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15\text{ V}, V_- = -15\text{ V}$ $V_L = 5\text{ V}, V_{IN} = 2.4\text{ V}, 0.8\text{ V}^f$		Temp <sup>b</sup>	Typ <sup>c</sup>	A Suffix -55 to 125°C		D Suffix -40 to 85°C		Unit
						Min <sup>d</sup>	Max <sup>d</sup>	Min <sup>d</sup>	Max <sup>d</sup>	
<b>Analog Switch</b>										
Analog Signal Range <sup>e</sup>	$V_{ANALOG}$			Full		-15	15	-15	15	V
Drain-Source On-Resistance	$r_{DS(on)}$	$I_S = -10\text{ mA}, V_D = \pm 12.5\text{ V}$ $V_+ = 13.5\text{ V}, V_- = -13.5\text{ V}$		Room Full	20		35 45		35 45	$\Omega$
Switch Off Leakage Current	$I_{S(off)}$	$V_+ = 16.5\text{ V}, V_- = -16.5\text{ V}$ $V_D = \mp 15.5\text{ V}$ $V_S = \pm 15.5\text{ V}$		Room Full	-0.1	-0.25 -20	0.25 20	-0.25 -5	0.25 5	nA
	$I_{D(off)}$		DG417 DG418	Room Full	-0.1	-0.25 -20	0.25 20	-0.25 -5	0.25 5	
			DG419	Room Full	-0.1	-0.75 -60	0.75 60	-0.75 -12	0.75 12	
Channel On Leakage Current	$I_{D(on)}$	$V_+ = 16.5\text{ V}, V_- = -16.5\text{ V}$ $V_S = V_D = \pm 15.5\text{ V}$		DG417 DG418	Room Full	-0.4	-0.4 -40	0.4 40	-0.4 -10	0.4 10
				DG419	Room Full	-0.4	-0.75 -60	0.75 60	-0.75 -12	0.75 12
<b>Digital Control</b>										
Input Current $V_{IN}$ Low	$I_{IL}$			Full	0.005	-0.5	0.5	-0.5	0.5	$\mu\text{A}$
Input Current $V_{IN}$ High	$I_{IH}$			Full	0.005	-0.5	0.5	-0.5	0.5	
<b>Dynamic Characteristics</b>										
Turn-On Time	$t_{ON}$	$R_L = 300\ \Omega, C_L = 35\text{ pF}$ $V_S = \pm 10\text{ V}$ See Switching Time Test Circuit		DG417 DG418	Room Full	100		175 250		175 250
Turn-Off Time	$t_{OFF}$			DG417 DG418	Room Full	60		145 210		145 210
Transition Time	$t_{TRANS}$	$R_L = 300\ \Omega, C_L = 35\text{ pF}$ $V_{S1} = \pm 10\text{ V}$ $V_{S2} = \mp 10\text{ V}$		DG419	Room Full			175 250		175 250
Break-Before-Make Time Delay	$t_D$	$R_L = 300\ \Omega, C_L = 35\text{ pF}$ $V_{S1} = V_{S2} = \pm 10\text{ V}$		DG419	Room	13	5		5	
Charge Injection	Q	$C_L = 10\text{ nF}, V_{gen} = 0\text{ V}, R_{gen} = 0\ \Omega$		Room	60					pC
Source Off Capacitance	$C_{S(off)}$	$f = 1\text{ MHz}, V_S = 0\text{ V}$		Room	8					pF
Drain Off Capacitance	$C_{D(off)}$			DG417 DG418	Room	8				
Channel On Capacitance	$C_{D(on)}$			DG417 DG418	Room	30				
				DG419	Room	35				
<b>Power Supplies</b>										
Positive Supply Current	$I_+$	$V_+ = 16.5\text{ V}, V_- = -16.5\text{ V}$ $V_{IN} = 0\text{ or }5\text{ V}$		Room Full	0.001		1 5		1 5	$\mu\text{A}$
Negative Supply Current	$I_-$			Room Full	-0.001	-1 -5		-1 -5		
Logic Supply Current	$I_L$			Room Full	0.001		1 5		1 5	
Ground Current	$I_{GND}$			Room Full	-0.000 1	-1 -5		-1 -5		

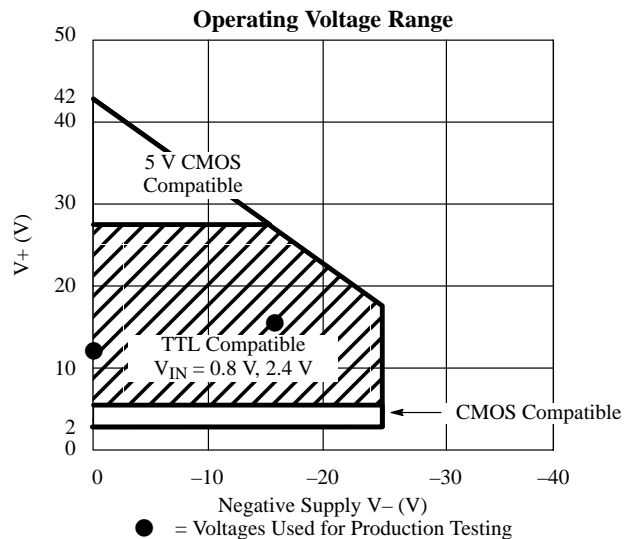
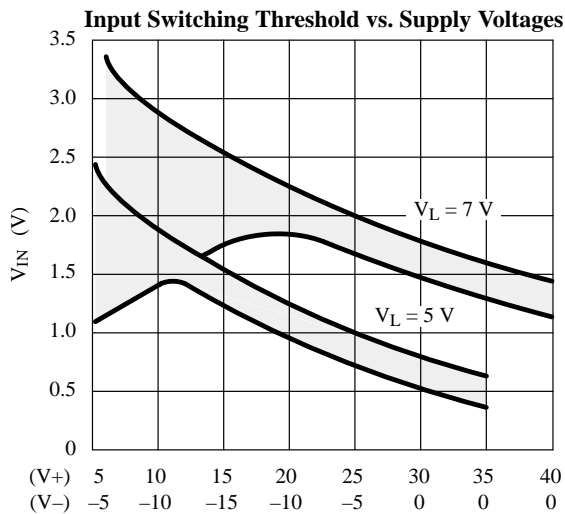
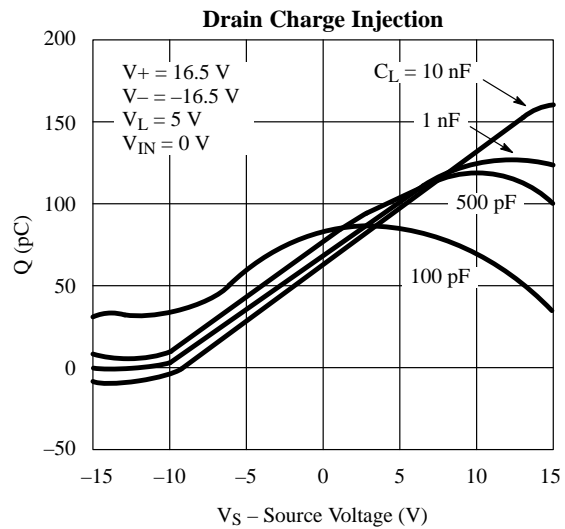
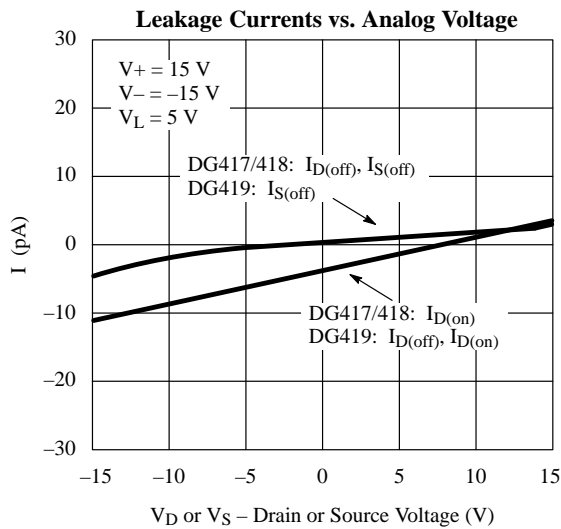
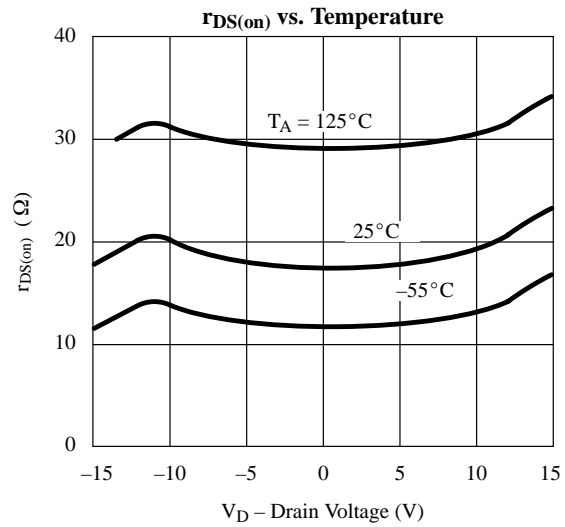
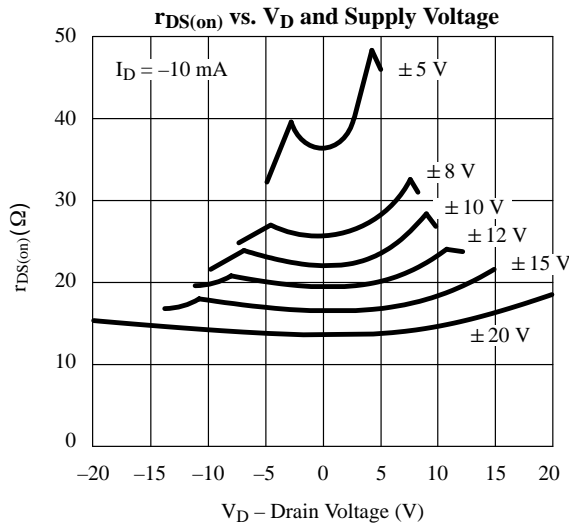
## Specifications<sup>a</sup> for Unipolar Supplies

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 12\text{ V}$ , $V_- = 0\text{ V}$ $V_L = 5\text{ V}$ , $V_{IN} = 2.4\text{ V}$ , $0.8\text{ V}^f$		Temp <sup>b</sup>	Typ <sup>c</sup>	A Suffix -55 to 125°C		D Suffix -40 to 85°C		Unit
						Min <sup>d</sup>	Max <sup>d</sup>	Min <sup>d</sup>	Max <sup>d</sup>	
<b>Analog Switch</b>										
Analog Signal Range <sup>e</sup>	$V_{ANALOG}$			Full		0	12	0	12	V
Drain-Source On-Resistance	$r_{DS(on)}$			Room	40					$\Omega$
<b>Dynamic Characteristics</b>										
Turn-On Time	$t_{ON}$	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ , $V_S = 8\text{ V}$ See Switching Time Test Circuit		Room	110					ns
Turn-Off Time	$t_{OFF}$			Room	40					
Break-Before-Make Time Delay	$t_D$	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$	DG419	Room	60					
Charge Injection	Q	$C_L = 10\text{ nF}$ , $V_{gen} = 0\text{ V}$ , $R_{gen} = 0\ \Omega$		Room	5					pC
<b>Power Supplies</b>										
Positive Supply Current	$I_+$	$V_+ = 13.2\text{ V}$ , $V_L = 5.25\text{ V}$ $V_{IN} = 0\text{ or }5\text{ V}$		Room	0.001					$\mu\text{A}$
Negative Supply Current	$I_-$			Room	-0.001					
Logic Supply Current	$I_L$			Room	0.001					
Ground Current	$I_{GND}$			Room	-0.001					

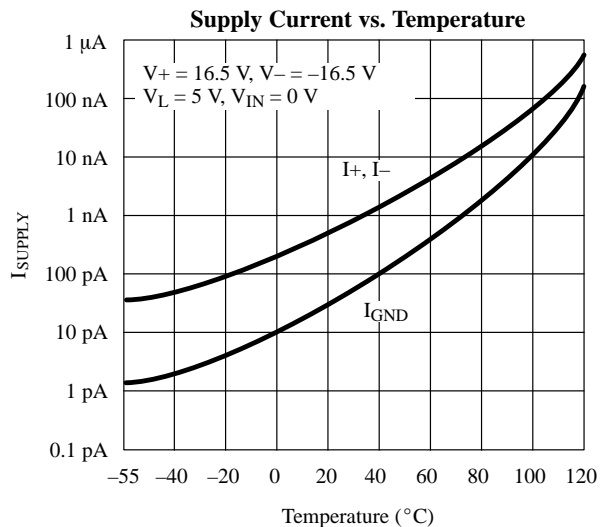
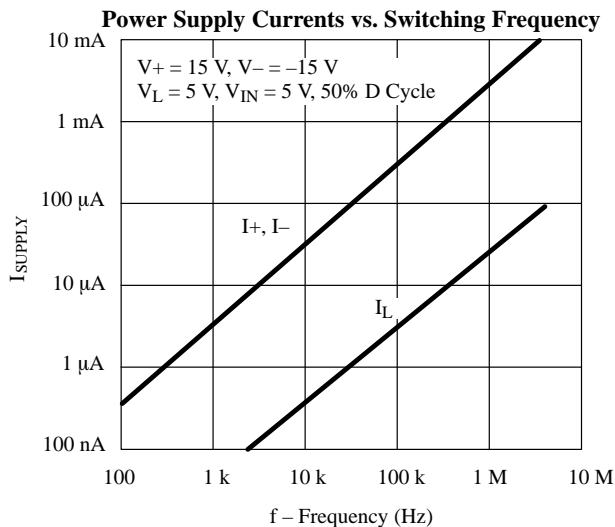
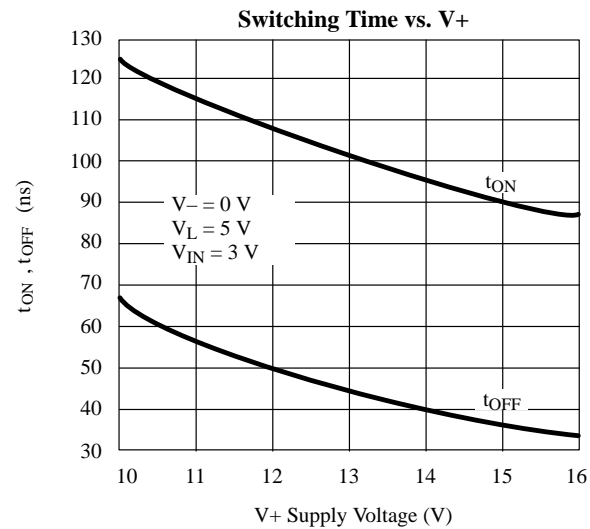
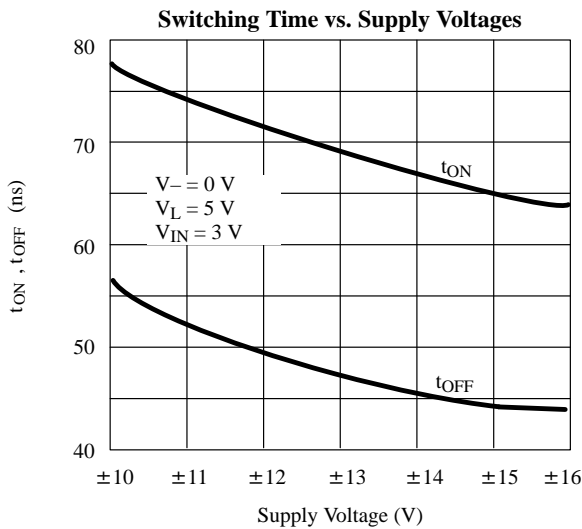
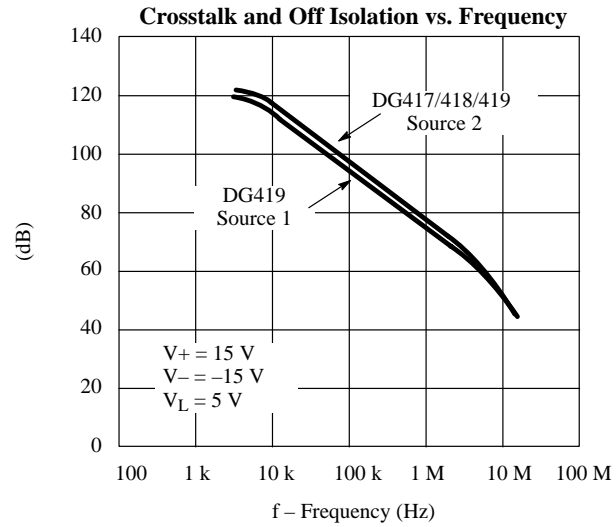
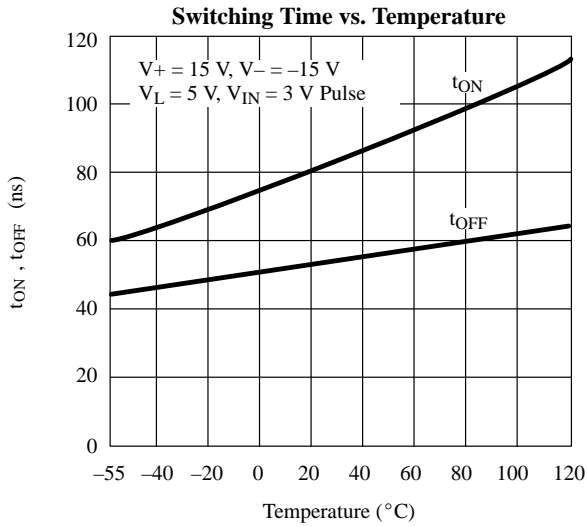
Notes:

- Refer to PROCESS OPTION FLOWCHART.
- Room = 25°C, Full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guaranteed by design, not subject to production test.
- $V_{IN}$  = input voltage to perform proper function.

## Typical Characteristics

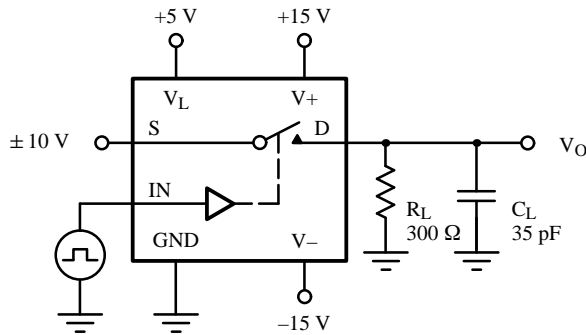


## Typical Characteristics (Cont'd)



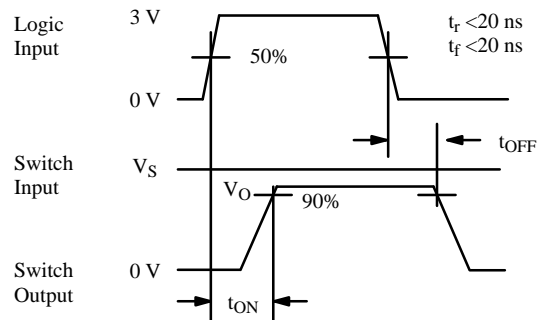
## Test Circuits

$V_O$  is the steady state output with the switch on.



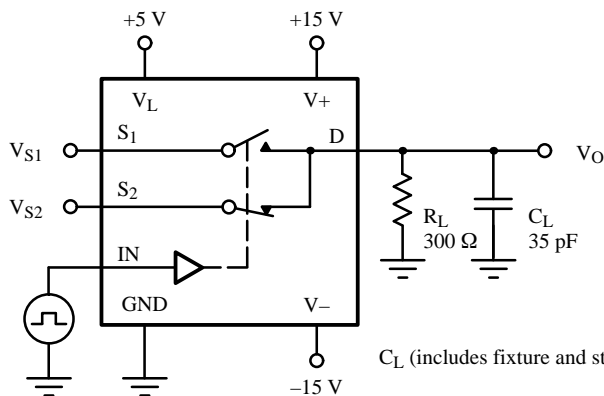
$C_L$  (includes fixture and stray capacitance)

$$V_O = V_S \frac{R_L}{R_L + r_{DS(on)}}$$

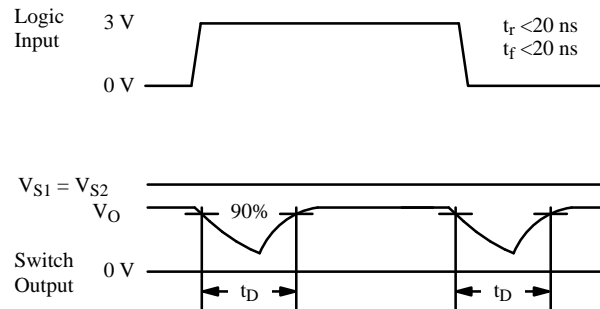


Note: Logic input waveform is inverted for switches that have the opposite logic sense.

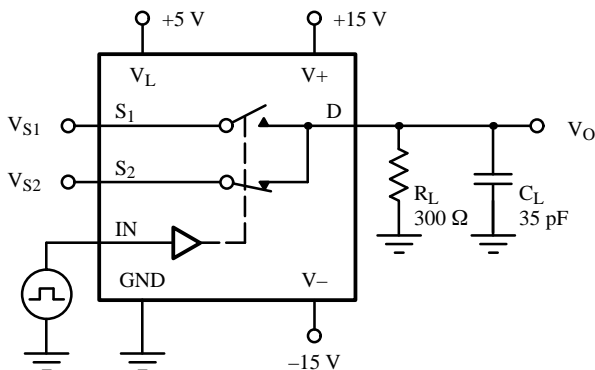
**Figure 2.** Switching Time (DG417/418)



$C_L$  (includes fixture and stray capacitance)

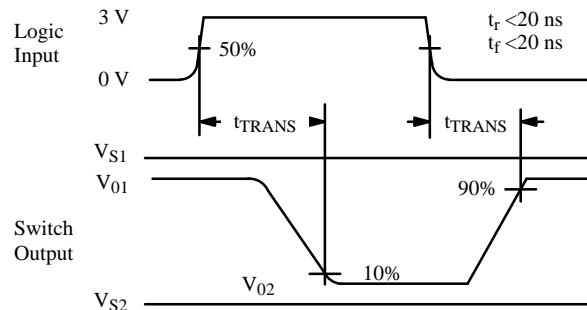


**Figure 3.** Break-Before-Make (DG419)



$C_L$  (includes fixture and stray capacitance)

$$V_O = V_S \frac{R_L}{R_L + r_{DS(on)}}$$



**Figure 4.** Transition Time (DG419)

## Test Circuits (Cont'd)

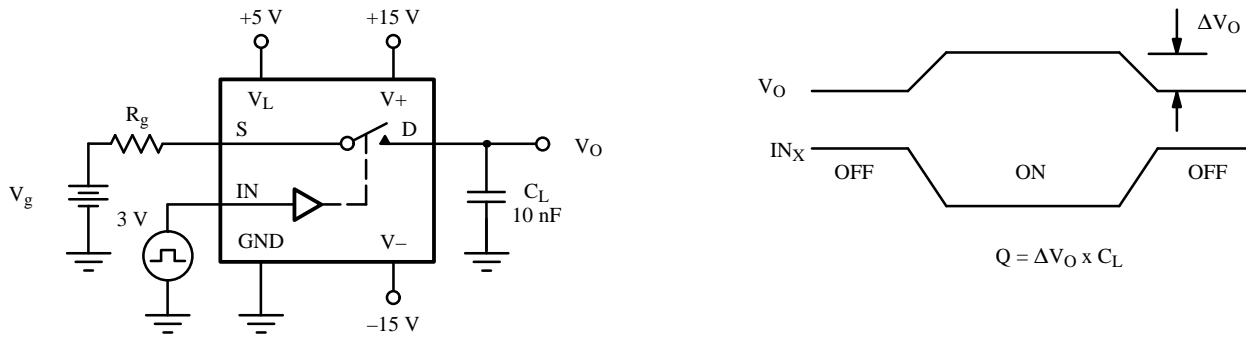


Figure 5. Charge Injection

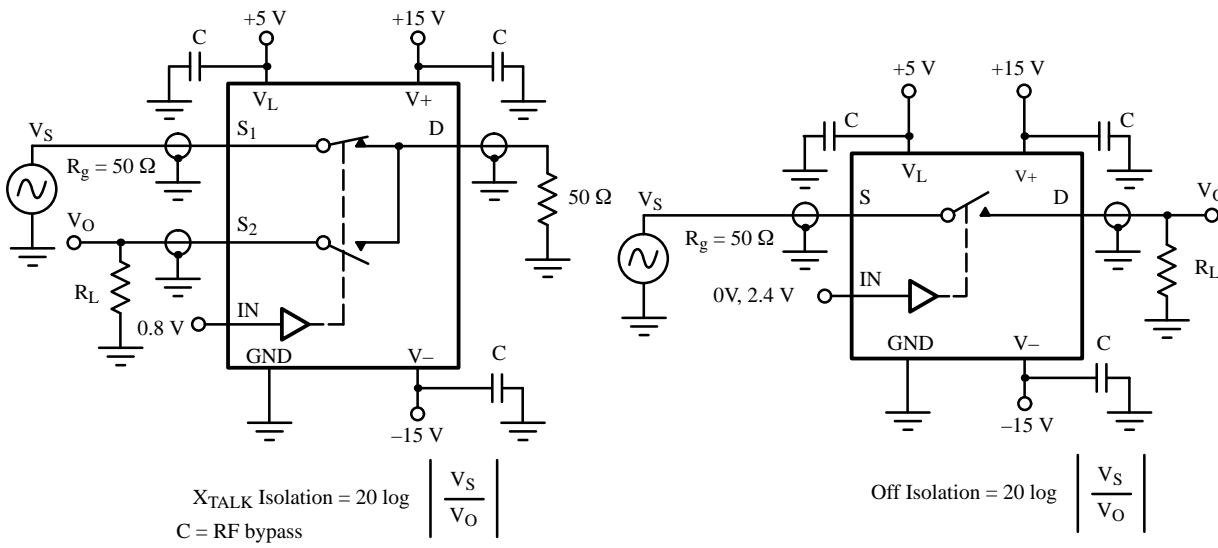


Figure 6. Crosstalk (DG419)

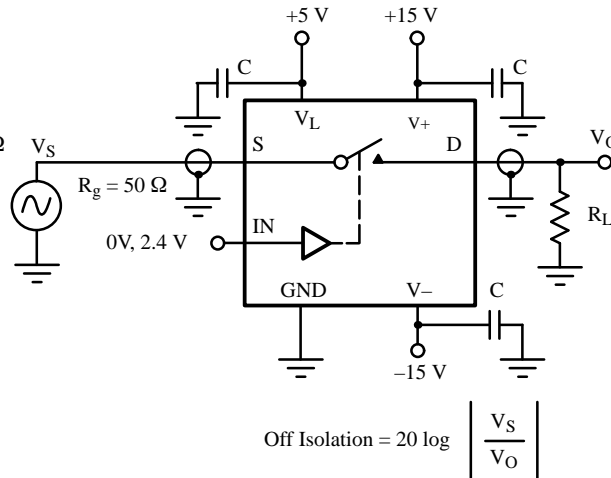


Figure 7. Off Isolation

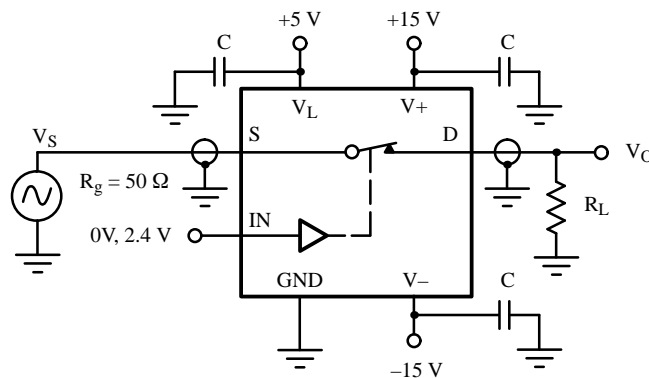
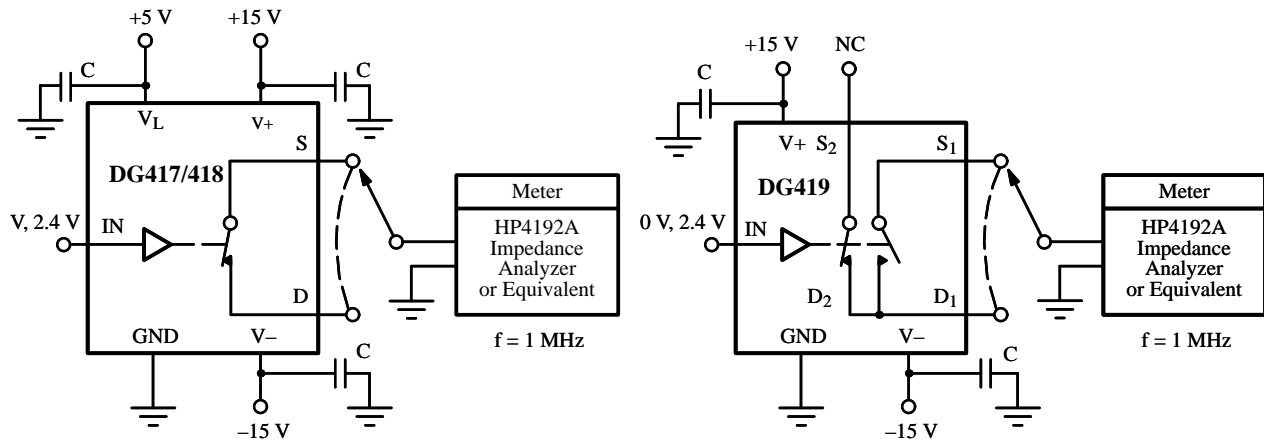


Figure 8. Insertion Loss



**Test Circuits (Cont'd)**



**Figure 9.** Source/Drain Capacitances

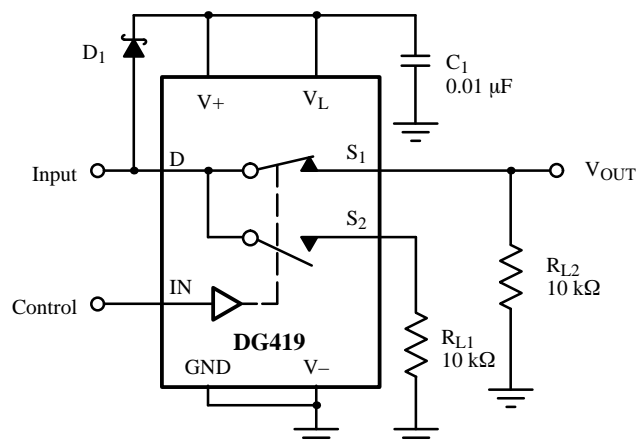
**Applications**

**Switched Signal Powers Analog Switch**

The analog switch in Figure 10 derives power from its input signal, provided the input signal amplitude exceeds 4 V and its frequency exceeds 1 kHz.

This circuit is useful when signals have to be routed to either of two remote loads. Only three conductors are required: one for the signal to be switched, one for the control signal and a common return.

A positive input pulse turns on the clamping diode  $D_1$  and charges  $C_1$ . The charge stored on  $C_1$  is used to power the chip; operation is satisfactory because the switch requires less than 1  $\mu\text{A}$  of stand-by supply current. Loading of the signal source is imperceptible. The DG419's on-resistance is a low 100  $\Omega$  for a 5-V input signal.



**Figure 10.** Switched Signal Powers Remote SPDT Analog Switch

## Applications (Cont'd)

### Micropower UPS Transfer Switch

When  $V_{CC}$  drops to 3.3 V, the DG417 changes states, closing  $SW_1$  and connecting the backup cell, as shown in Figure 11.  $D_1$  prevents current from leaking back towards the rest of the circuit. Current consumption by the CMOS analog switch is around 100 pA; this ensures that most of the power available is applied to the memory, where it is really needed. In the stand-by mode, hundreds of  $\mu A$  are sufficient to retain memory data.

When the 5-V supply comes back up, the resistor divider senses the presence of at least 3.5 V, and causes a new

change of state in the analog switch, restoring normal operation.

### Programmable Gain Amplifier

The DG419, as shown in Figure 12, allows accurate gain selection in a small package. Switching into virtual ground reduces distortion caused by  $r_{DS(on)}$  variation as a function of analog signal amplitude.

### GaAs FET Driver

The DG419, as shown in Figure 13 may be used as a GaAs FET driver. It translates a TTL control signal into  $-8$ -V, 0-V level outputs to drive the gate.

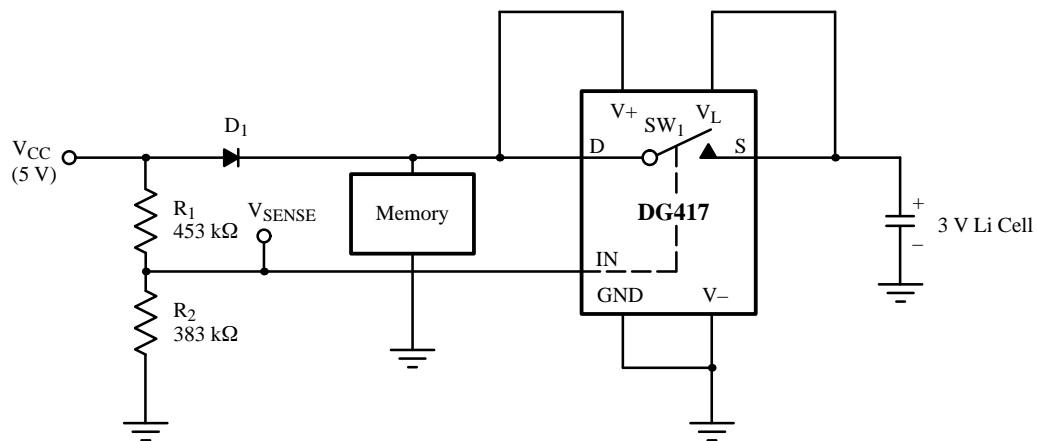


Figure 11. Micropower UPS Circuit

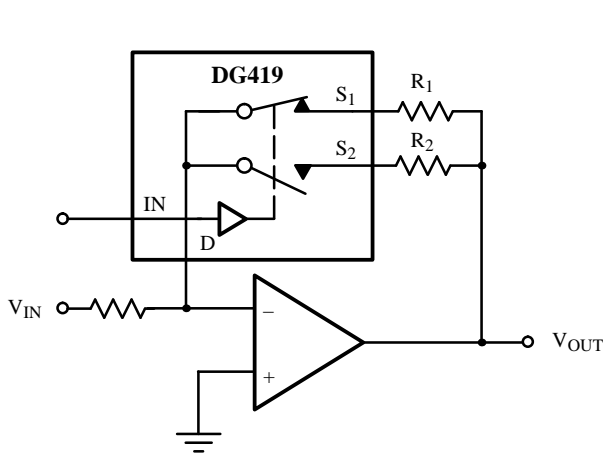


Figure 12. Programmable Gain Amplifier

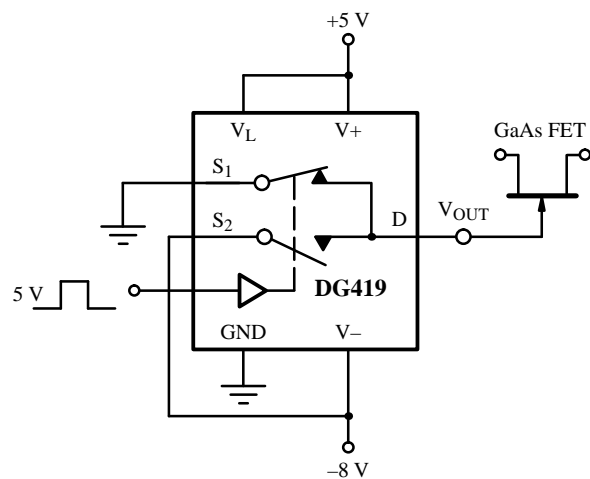


Figure 13. GaAs FET Driver